

# isc N-Channel MOSFET Transistor

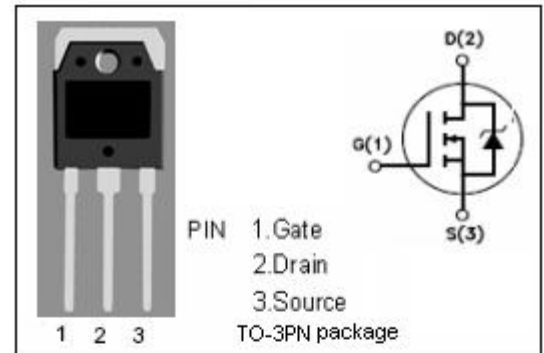
## 2SK1940-01

### DESCRIPTION

- Drain Current  $-I_D = 12A @ T_C = 25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS} = 600V(\text{Min})$
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

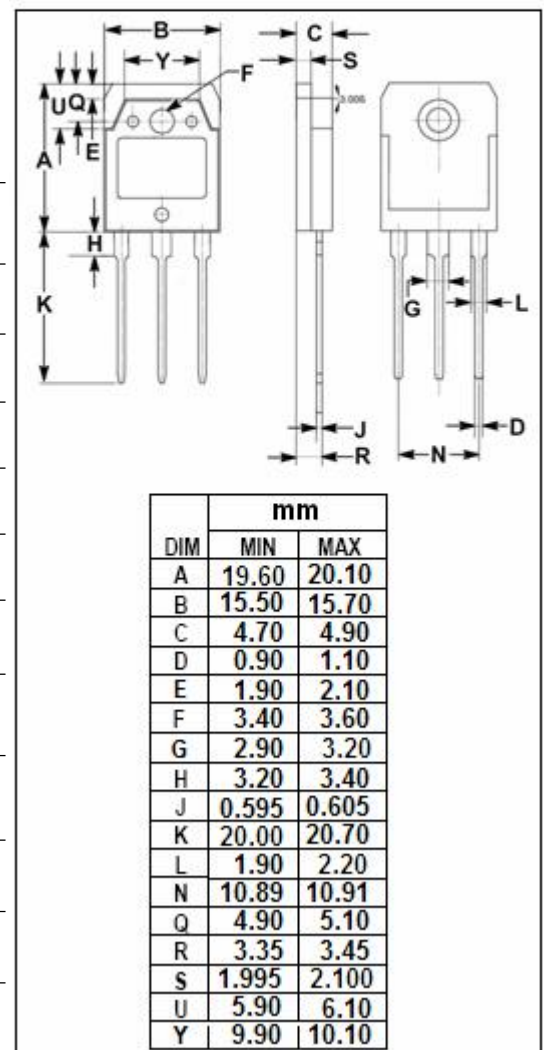
### APPLICATIONS

- Switching regulator
- UPS
- DC-DC converters
- General purpose power amplifier



### ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ C$ )

| SYMBOL    | PARAMETER                                 | VALUE    | UNIT       |
|-----------|---|----------|------------|
| $V_{DSS}$ | Drain-Source Voltage ( $V_{GS}=0$ )       | 600      | V          |
| $V_{GS}$  | Gate-Source Voltage                       | $\pm 30$ | V          |
| $I_D$     | Drain Current-continuous@ $TC=25^\circ C$ | 12       | A          |
| $I_{DM}$  | Drain Current-Single Pulsed               | 48       | A          |
| $P_{tot}$ | Total Dissipation@ $TC=25^\circ C$        | 125      | W          |
| $T_j$     | Max. Operating Junction Temperature       | 150      | $^\circ C$ |
| $T_{stg}$ | Storage Temperature Range                 | -55~150  | $^\circ C$ |



### • THERMAL CHARACTERISTICS

| SYMBOL        | PARAMETER                               | MAX  | UNIT         |
|---------------|---|------|--------------|
| $R_{th\ j-c}$ | Thermal Resistance, Junction to Case    | 1.25 | $^\circ C/W$ |
| $R_{th\ j-a}$ | Thermal Resistance, Junction to Ambient | 35   | $^\circ C/W$ |

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• ELECTRICAL CHARACTERISTICS (T<sub>c</sub>=25°C)

| SYMBOL               | PARAMETER                       | CONDITIONS   | MIN | TYPE | MAX  | UNIT |
|----------------------|---------------------------------|--|-----|------|------|------|
| V <sub>(BR)DSS</sub> | Drain-Source Breakdown Voltage  | V <sub>GS</sub> = 0; I <sub>D</sub> = 1mA  | 600 |      |      | V    |
| V <sub>GS(th)</sub>  | Gate Threshold Voltage          | V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =1mA                                    | 2.5 |      | 3.5  | V    |
| R <sub>DS(on)</sub>  | Drain-Source On-Resistance      | V <sub>GS</sub> = 10V; I <sub>D</sub> = 6A   |     |      | 0.75 | Ω    |
| I <sub>GSS</sub>     | Gate-Body Leakage Current       | V <sub>GS</sub> = ±30V; V <sub>DS</sub> = 0  |     |      | ±100 | nA   |
| I <sub>DSS</sub>     | Zero Gate Voltage Drain Current | V <sub>DS</sub> = 600V; V <sub>GS</sub> = 0  |     | 10   | 500  | μA   |
| V <sub>SD</sub>      | Forward On-Voltage              | I <sub>S</sub> =24A; V <sub>GS</sub> =0  |     |      | 1.58 | V    |
| G <sub>fs</sub>      | Forward Transconductance        | V <sub>DS</sub> = 25V; I <sub>D</sub> =6A  | 6.0 |      |      | S    |
| t <sub>r</sub>       | Rise time                       | V <sub>GS</sub> =10V; I <sub>D</sub> =6A;<br>V <sub>DD</sub> =300V;<br>R <sub>L</sub> =10Ω |     | 60   | 90   | ns   |
| t <sub>on</sub>      | Turn-on time                    |  |     | 30   | 45   |      |
| t <sub>f</sub>       | Fall time                       |  |     | 80   | 120  |      |
| t <sub>off</sub>     | Turn-off time                   |  |     | 140  | 210  |      |

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